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Jang et al.

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(54) **ORGANIC LIGHT EMITTING DISPLAY DEVICE HAVING CATHODE ELECTRODE CONNECTED WITH AN AUXILIARY ELECTRODE VIA A GAP SPACE BETWEEN THE FIRST AND SECOND BANKS**

(58) **Field of Classification Search**

CPC H01L 27/3245; H01L 27/3248; H01L 51/5068; H01L 51/5084; H01L 51/5206; H01L 51/5228

See application file for complete search history.

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ABSTRACT

An organic light emitting display device can include a substrate; an anode electrode on the substrate; an organic emitting layer on the anode electrode; a cathode electrode on the organic emitting layer; an auxiliary electrode connected with the cathode electrode; a first bank on an upper surface of the auxiliary electrode; and a second bank disposed between the auxiliary electrode and the anode electrode, in which the second bank is formed of a same material as the first bank, and the first and second banks are spaced apart from each other, and a width of an upper surface of the first bank is larger than a width of a lower surface of the first bank, and the cathode electrode is connected with the auxiliary electrode via a gap space between the first bank and the second bank.

17 Claims, 7 Drawing Sheets

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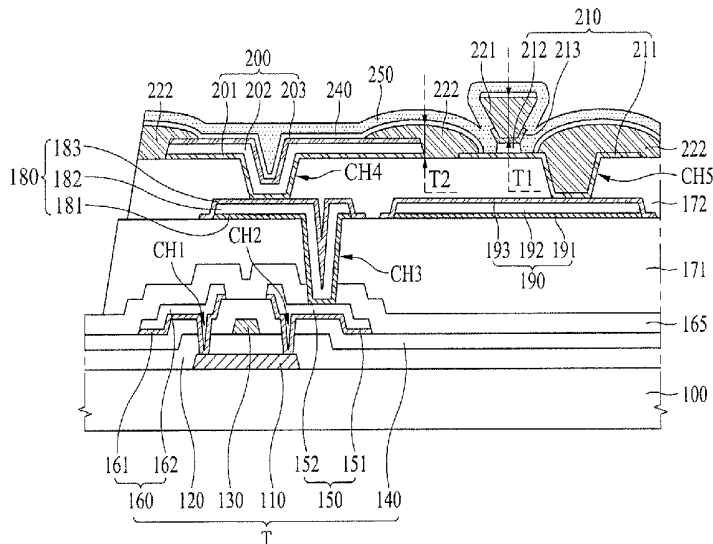
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H01L 51/00 (2006.01)
H01L 51/52 (2006.01)
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(52) **U.S. Cl.**

CPC **H01L 27/3246** (2013.01); **H01L 51/0023** (2013.01); **H01L 51/5203** (2013.01); **H01L 51/5228** (2013.01); **H01L 51/56** (2013.01)



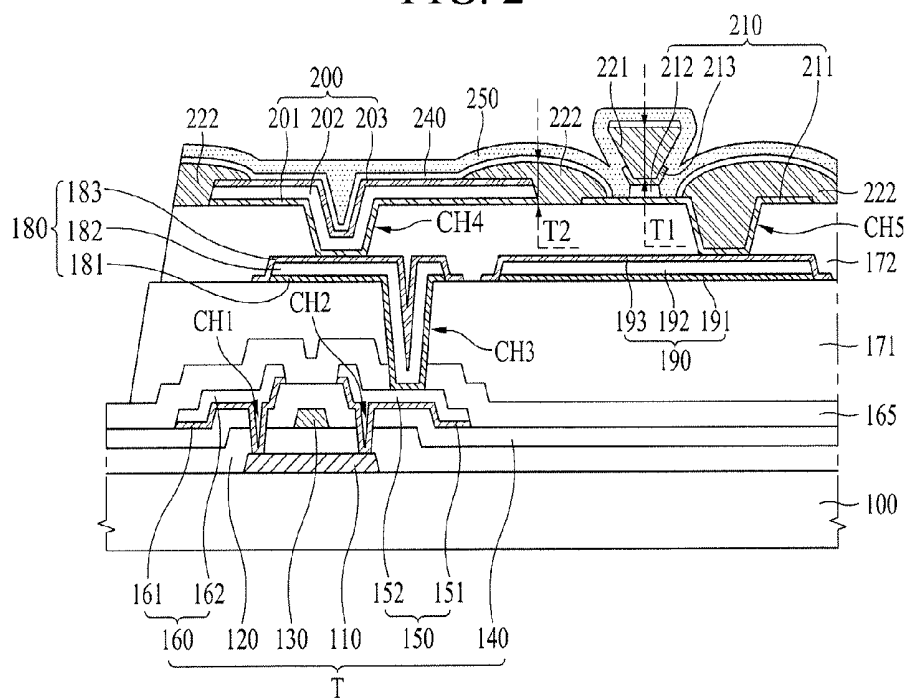


FIG. 3A

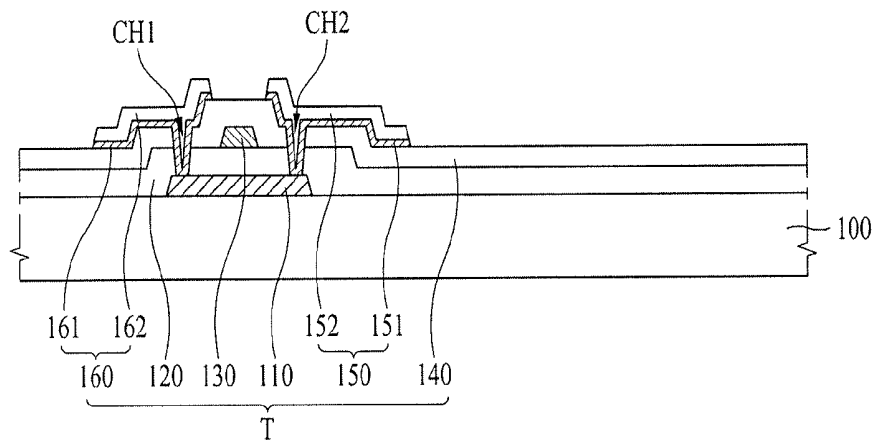


FIG. 3B

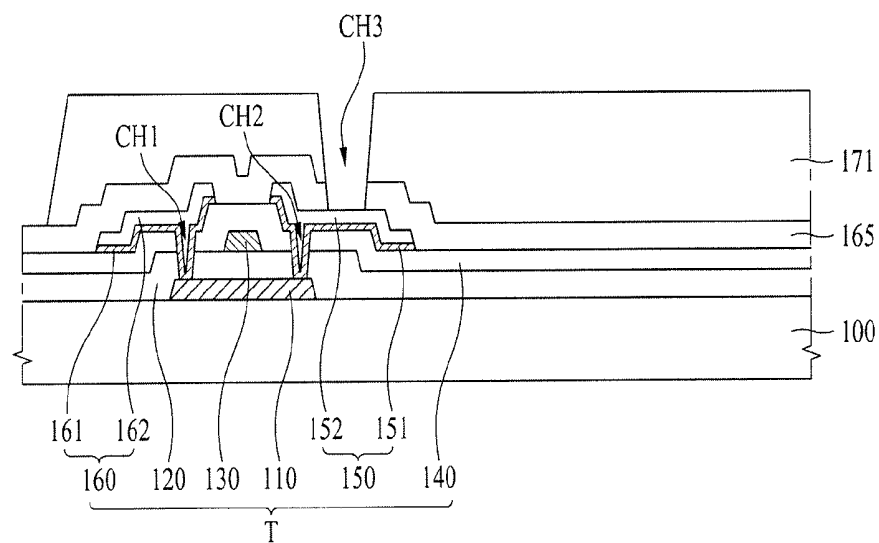


FIG. 3C

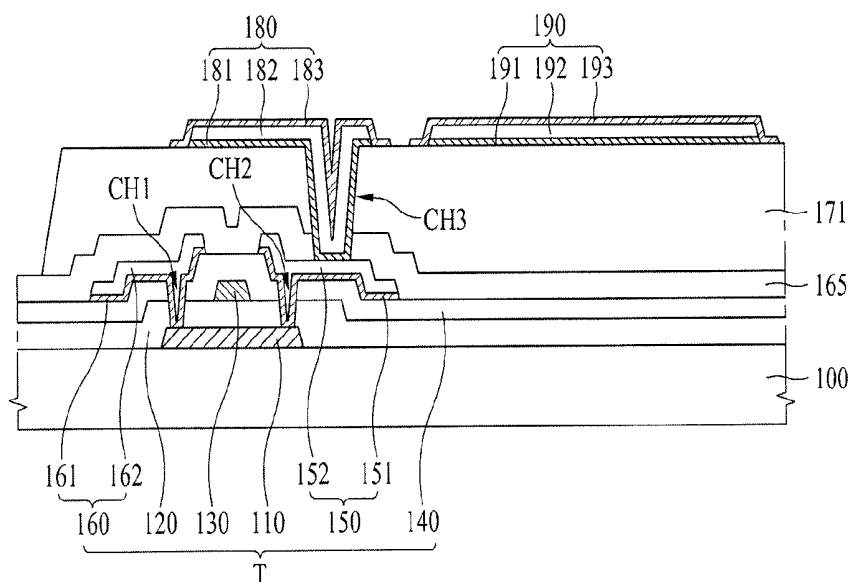


FIG. 3D

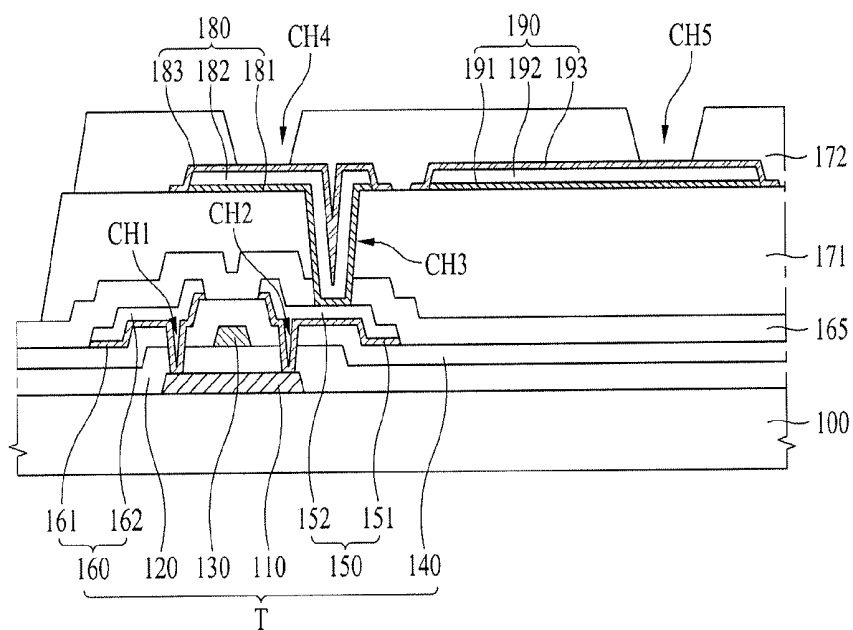


FIG. 3E

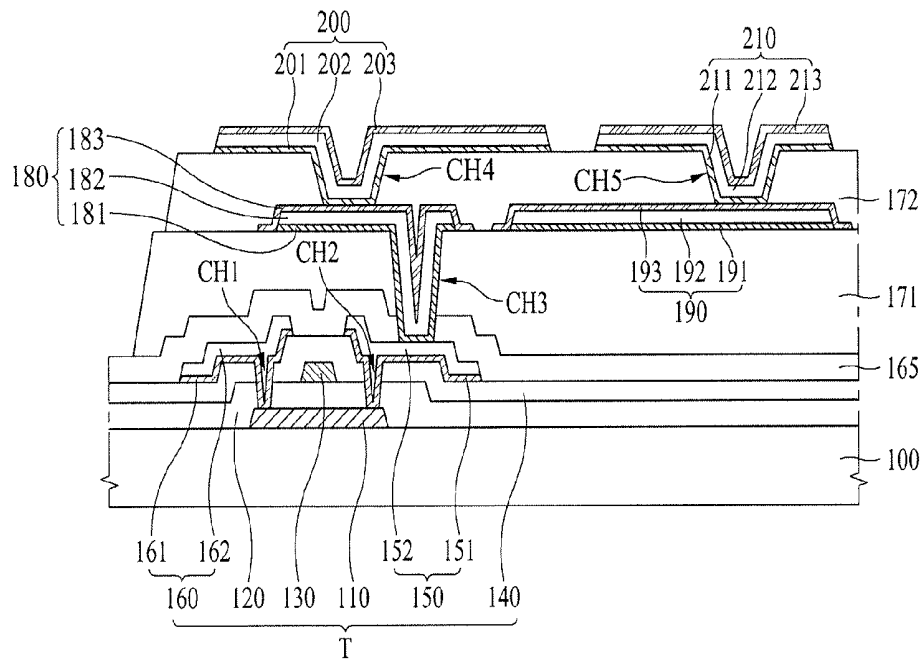


FIG. 3F

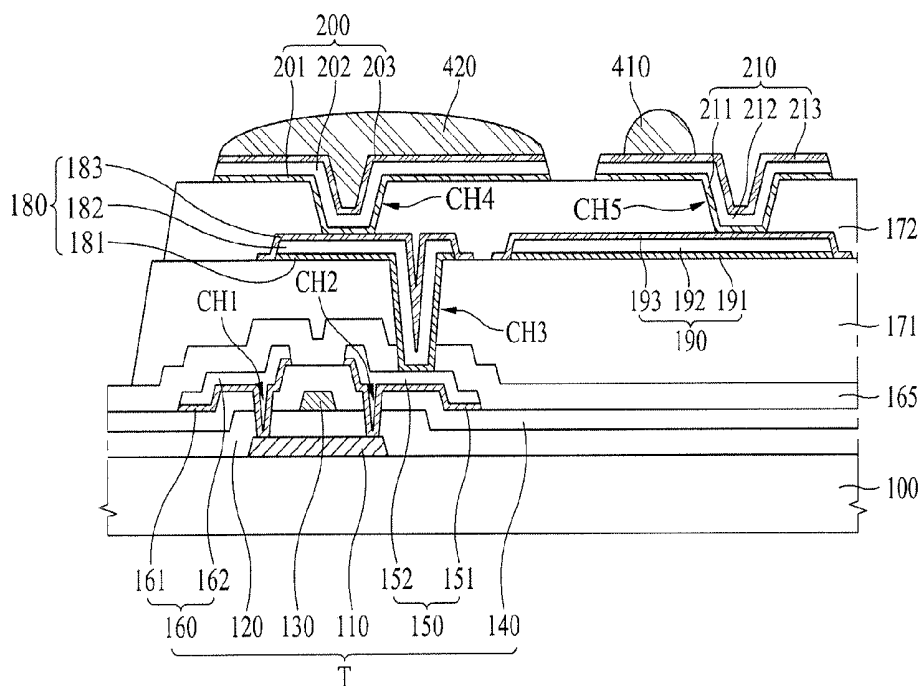


FIG. 3I

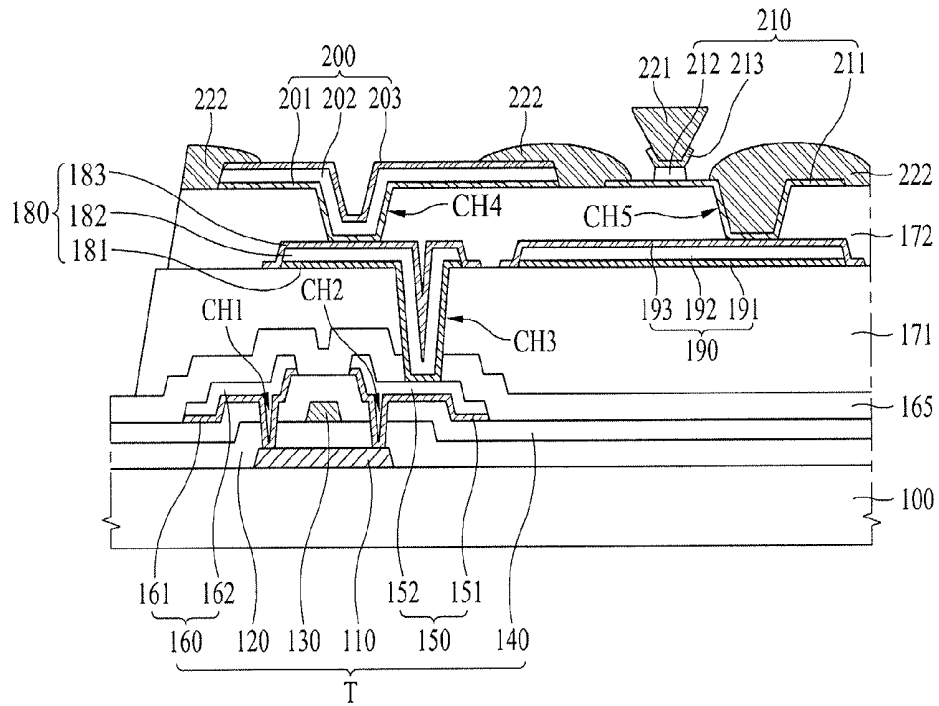


FIG. 3J

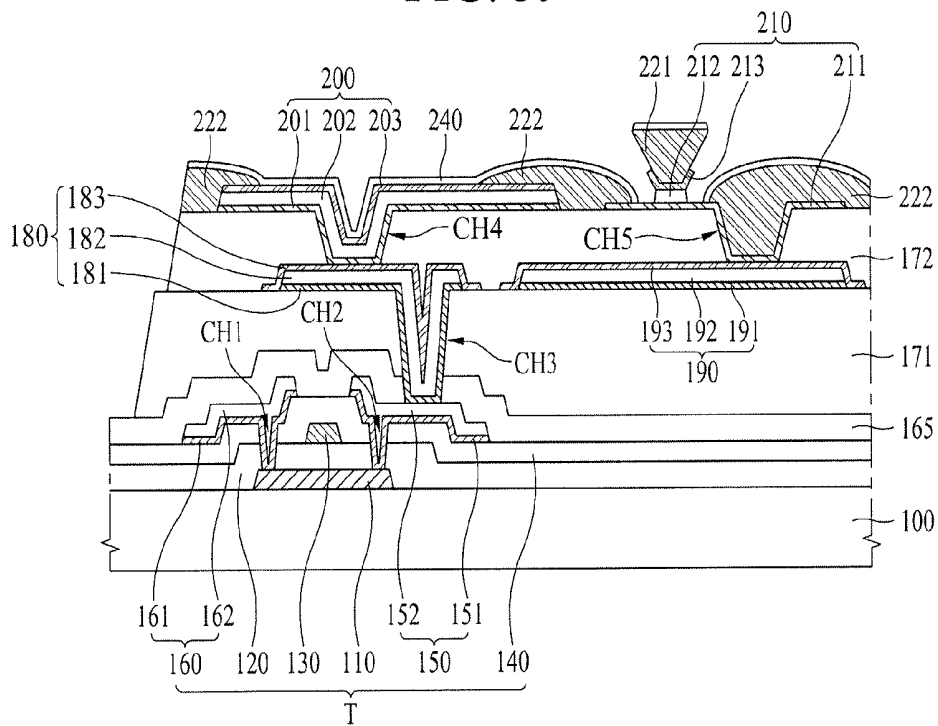
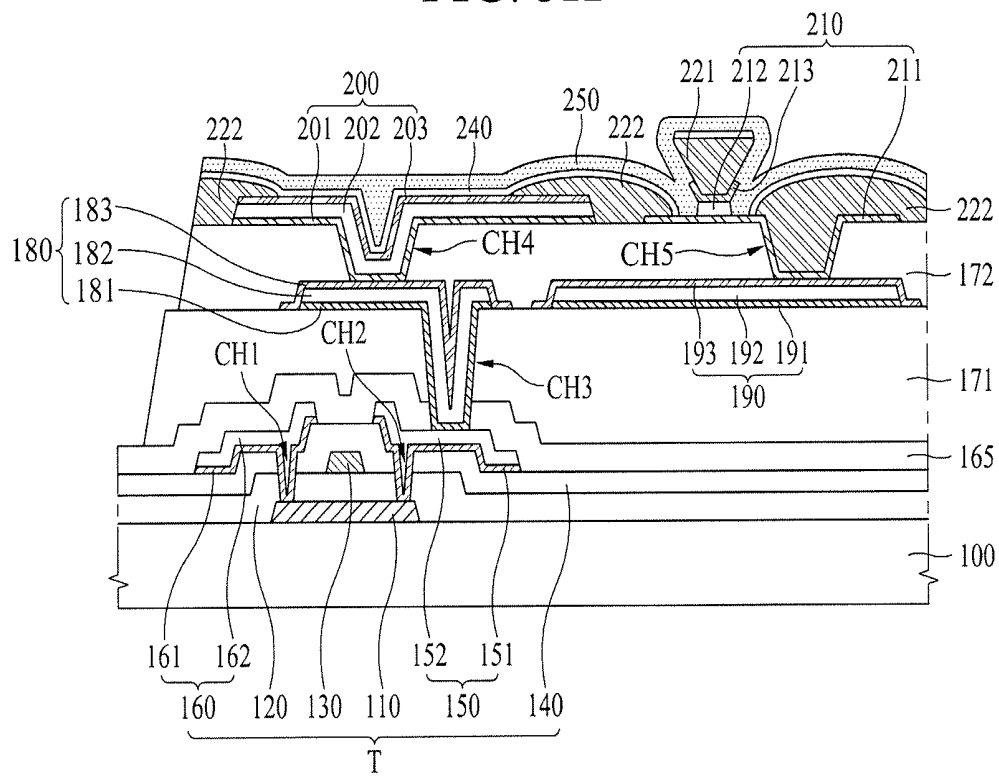


FIG. 3K



**ORGANIC LIGHT EMITTING DISPLAY
DEVICE HAVING CATHODE ELECTRODE
CONNECTED WITH AN AUXILIARY
ELECTRODE VIA A GAP SPACE BETWEEN
THE FIRST AND SECOND BANKS**

CROSS REFERENCE TO RELATED
APPLICATIONS

This application claims the benefit of the Korean Patent Application No. 10-2015-0181241 filed in the Republic of Korea on Dec. 17, 2015, which is hereby incorporated by reference as if fully set forth herein.

BACKGROUND OF THE INVENTION

Field of the Disclosure

Embodiments of the present invention relate to an organic light emitting display device, and more particularly, to a top emission type organic light emitting display device, and a method of manufacturing the same.

Discussion of the Related Art

An organic light emitting display (OLED) device, which is a self-light emitting display device, has advantages of low power consumption, rapid response speed, high emission efficiency, high luminance and wide viewing angle.

According to the direction of light emitted from an organic light emitting device, the OLED device may be generally classified into a top emission type and a bottom emission type. In the bottom emission type, a circuit device is disposed between an emitting layer and an image displaying surface, which may lower an aperture ratio of the OLED device. In the top emission type, a circuit device is not disposed between an emitting layer and an image displaying surface, thus an aperture ratio may be improved when compared to the bottom emission type.

FIG. 1 is a cross sectional view of a related art top emission type OLED device.

As shown in FIG. 1, a thin film transistor layer (T) including an active layer 11, a gate insulating film 12, a gate electrode 13, an insulating interlayer 14, a source electrode 15, and a drain electrode 16 is provided on a substrate 10, and then a passivation layer 20 and a planarization layer 30 are sequentially provided on the thin film transistor layer (T).

Also, an anode electrode 40 and an auxiliary electrode 50 are provided on the planarization layer 30. The auxiliary electrode 50 is provided to lower a resistance of a cathode electrode 90. In the top emission type, light emitted from an organic emitting layer 80 passes through the cathode electrode 90. In this reason, the cathode electrode 90 is formed of a transparent conductive material, which causes the increase of resistance therein. In order to lower the resistance of the cathode electrode 90, the cathode electrode 90 is connected with the auxiliary electrode 50.

On the anode electrode 40 and the auxiliary electrode 50, a bank 60 is provided to define a pixel region. Also, the organic emitting layer 80 is provided in the pixel region defined by the bank 60.

If the auxiliary electrode 50 is covered by the organic emitting layer 80, an electrical connection between the cathode electrode 90 and the auxiliary electrode 50 becomes difficult. Thus, in order to prevent the auxiliary electrode 50 from being covered by the organic emitting layer 80, a partition 70 is provided on the auxiliary electrode 50. The partition 70 is spaced apart from the bank 60, whereby the

auxiliary electrode 50 and the cathode electrode 90 are connected to each other via a space between the partition 70 and the bank 60.

The partition 70 can include a first partition 71 and a second partition 72, in which the partition 70 is formed in a structure of eaves. Thus, according as the organic emitting layer 80 with superior straightness for the properties of process is blocked by the partition 70, it is possible to prevent the organic emitting layer 80 from being permeated into the space between the partition 70 and the bank 60. Meanwhile, the cathode electrode 90 with inferior straightness for the properties of process permeates into the space between the partition 70 and the bank 60, and is then connected to the auxiliary electrode 50.

In the related art top emission type OLED device, the partition 70 is provided to allow an electrical connection between the cathode electrode 90 and the auxiliary electrode 50. Accordingly, an additional mask process for forming the partition 70 is carried out, thereby causing a lower yield.

SUMMARY OF THE INVENTION

Accordingly, embodiments of the present invention are directed to a top emission type organic light emitting display device that substantially obviates one or more problems due to limitations and disadvantages of the related art, and a method of manufacturing the same.

An aspect of embodiments of the present invention is directed to providing a top emission type organic light emitting display device which enables an electrical connection between a cathode electrode and an auxiliary electrode without forming an additional partition, and a method of manufacturing the same.

Additional advantages and features of embodiments of the invention will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of embodiments of the invention. The objectives and other advantages of embodiments of the invention may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

To achieve these and other advantages and in accordance with the purpose of embodiments of the invention, as embodied and broadly described herein, there is provided an organic light emitting display device that can include anode and cathode electrodes on a substrate, an organic emitting layer provided between the anode electrode and the cathode electrode, an auxiliary electrode connected with the cathode electrode, a first bank on the auxiliary electrode, and a second bank between the auxiliary electrode and the anode electrode, in which the first and second banks are spaced from each other, and a width in an upper surface of the first bank is larger than a width in a lower surface of the first bank, and the cathode electrode is connected with the auxiliary electrode via a gap space between the first bank and the second bank.

In another aspect of an embodiment of the present invention, there is provided a method of manufacturing an organic light emitting display device that can include providing an anode electrode and an auxiliary electrode on a substrate, providing a first bank on the auxiliary electrode, and providing a second bank between the auxiliary electrode and the anode electrode, in which the second bank is spaced from the first bank, providing an organic emitting layer on the anode electrode, and providing a cathode electrode on the organic emitting layer, and a width in an upper surface of the

first bank is larger than a width in a lower surface of the first bank, and the cathode electrode is connected with the auxiliary electrode via a gap space between the first bank and the second bank.

It is to be understood that both the foregoing general description and the following detailed description of embodiments of the present invention are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are included to provide a further understanding of embodiments of the invention and are incorporated in and constitute a part of this application, illustrate embodiment(s) of the invention and together with the description serve to explain the principle of embodiments of the invention. In the drawings:

FIG. 1 is a cross sectional view illustrating a related art top emission type organic light emitting display device;

FIG. 2 is a cross sectional view illustrating an organic light emitting display device according to an embodiment of the present invention; and

FIGS. 3A to 3K are cross sectional views illustrating a method of manufacturing the organic light emitting display device according to an embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

Reference will now be made in detail to the exemplary embodiments of the present invention, examples of which are illustrated in the accompanying drawings. Wherever possible, the same reference numbers will be used throughout the drawings to refer to the same or like parts. Advantages and features of the present invention, and implementation methods thereof will be clarified through following embodiments described with reference to the accompanying drawings. The present invention can, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the present invention to those skilled in the art. Further, the present invention is only defined by scopes of claims.

A shape, a size, a ratio, an angle, and a number disclosed in the drawings for describing embodiments of the present invention are merely an example, and thus, the present invention is not limited to the illustrated details. Like reference numerals refer to like elements throughout. In the following description, when the detailed description of the relevant known function or configuration is determined to unnecessarily obscure the important point of the present invention, the detailed description will be omitted. In a case where “comprise,” “have” and “include” are described in the present specification are used, another part may be added unless “only” is used. The terms of a singular form can include plural forms unless referred to the contrary.

In construing an element, the element is construed as including an error region although there is no explicit description.

In description of embodiments of the present invention, when a structure (for example, an electrode, a line, a wiring, a layer, or a contact) is described as being formed at an upper portion/lower portion of another structure or on/under the other structure, this description should be construed as

including a case where the structures contact each other and moreover, a case where a third structure is disposed therebetween.

In describing a temporal relationship, for example, when the temporal order is described as “after,” “subsequent,” “next” and “before” the order may not be continuous unless “just” or “directly” is used.

It will be understood that, although the terms “first,” “second,” etc. may be used herein to describe various elements, these elements should not be limited by these terms. These terms are only used to distinguish one element from another. For example, a first element could be termed a second element, and similarly, a second element could be termed a first element, without departing from the scope of the present invention.

Features of various embodiments of the present invention can be partially or overall coupled to or combined with each other, and can be variously inter-operated with each other and driven technically as those skilled in the art can sufficiently understand. The embodiments of the present invention may be carried out independently from each other, or can be carried out together in co-dependent relationship.

Hereinafter, an organic light emitting display device according to embodiments of the present invention will be described in detail with reference to the accompanying drawings.

FIG. 2 is a cross sectional view illustrating an organic light emitting display device according to one embodiment of the present invention.

As shown in FIG. 2, the organic light emitting display (OLED) device according to one embodiment of the present invention can include a substrate 100, a thin film transistor layer (T), a passivation layer 165, a first planarization layer 171, a second planarization layer 172, a first anode electrode 180, a second anode electrode 200, a first auxiliary electrode 190, a second auxiliary electrode 210, banks 221 and 222, an organic emitting layer 240, and a cathode electrode 250.

The substrate 100 may be formed of glass or transparent plastic, but the substrate 100 is not limited to these materials.

The thin film transistor layer (T) can include an active layer 110, a gate insulating film 120, a gate electrode 130, an insulating interlayer 140, a source electrode 150, and a drain electrode 160.

The active layer 110 is provided on the substrate 100, in which the active layer 110 overlaps with the gate electrode 130. The active layer 110 may be formed a silicon-based semiconductor material or oxide-based semiconductor material. Also, a light shielding layer may be additionally provided between the substrate 100 and the active layer 110. In this instance, external light, which is incident on a lower surface of the substrate 100, is blocked by the light shielding layer so that it is possible to prevent the active layer 110 from being damaged by the external light.

The gate insulating film 120 is provided on the active layer 110. The gate insulating film 120 insulates the active layer 110 and the gate electrode 130 from each other. For example, the gate insulating film 120 can be formed of an inorganic insulating material, and more particularly, the gate insulating film 120 can be formed in a single-layered structure of the inorganic insulating material such as silicon oxide SiO_x or silicon nitride SiN_x, or a multi-layered structure of the above silicon oxide SiO_x and silicon nitride SiN_x, but not limited to these structures.

The gate electrode 130 is provided on the gate insulating film 120. The gate electrode 130 overlaps with the active layer 110, wherein the gate insulating film 120 is interposed between the gate electrode 130 and the active layer 110

being overlapped with each other. The gate electrode **130** can be formed in a single-layered structure or multi-layered structure among molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu) and their alloys, but not limited to these materials.

The insulating interlayer **140** is provided on the gate electrode **130**. The insulating interlayer **140** is formed of the same material as that of the gate insulating film **120**. For example, the insulating interlayer **140** can be formed in a single-layered structure of the inorganic insulating material such as silicon oxide SiOx or silicon nitride SiNx, or a multi-layered structure of the above silicon oxide SiOx and silicon nitride SiNx, but not limited to these materials and structures.

The source electrode **150** and the drain electrode **160** confronting each other are provided on the insulating interlayer **140**. A first contact hole (CH1) for exposing one end of the active layer **110** is provided in the aforementioned gate insulating film **120** and the insulating interlayer **140**, and a second contact hole (CH2) for exposing the other end of the active layer **110** is provided in the aforementioned gate insulating film **120** and the insulating interlayer **140**. The source electrode **150** is connected to the other end of the active layer **110** via the second contact hole (CH2), and the drain electrode **160** is connected to one end of the active layer **110** via the first contact hole (CH1).

The source electrode **150** can include a lower source electrode **151** and an upper source electrode **152**.

The lower source electrode **151** is provided between the insulating interlayer **140** and the upper source electrode **152**, in which the lower source electrode **151** enhances an adhesive strength between the insulating interlayer **140** and the upper source electrode **152**. Also, the lower source electrode **151** protects a lower surface of the upper source electrode **152** so that it is possible to prevent the lower surface of the upper source electrode **152** from being corroded. Thus, an oxidation degree of the lower source electrode **151** can be lower than an oxidation degree of the upper source electrode **152**. That is, a corrosion resistance in a material of the lower source electrode **151** can be superior to a corrosion resistance in a material of the upper source electrode **152**. The lower source electrode **151** functions as an adhesion enhancement layer or a corrosion preventing layer. The lower source electrode **151** can be formed of an alloy MoTi of molybdenum and titanium, but not limited to this material.

The upper source electrode **152** is provided on an upper surface of the lower source electrode **151**. The upper source electrode **152** can be formed of a low-resistance metal material such as copper Cu, but not limited to this metal material. The upper source electrode **152** can be formed of a metal material whose resistance is relatively lower than that of the lower source electrode **151**. In order to lower a total resistance of the source electrode **150**, a thickness of the upper source electrode **152** is larger than a thickness of the lower source electrode **151**, preferably.

In the same way as the aforementioned source electrode **150**, the drain electrode **160** can include a lower drain electrode **161** and an upper drain electrode **162**.

The lower drain electrode **161** is provided between the insulating interlayer **140** and the upper drain electrode **162**, in which the lower drain electrode **161** enhances an adhesive strength between the insulating interlayer **140** and the upper drain electrode **162**. Also, the lower drain electrode **161** prevents a lower surface of the upper drain electrode **162** from being corroded. Thus, an oxidation degree of the lower

drain electrode **161** can be lower than an oxidation degree of the upper drain electrode **162**. That is, a corrosion resistance in a material of the lower drain electrode **161** can be superior to a corrosion resistance in a material of the upper drain electrode **162**. The lower drain electrode **161** can be formed of the same material as that of the aforementioned lower source electrode **151**, that is, alloy MoTi of molybdenum and titanium, but not limited to this material.

The upper drain electrode **162** is provided on an upper surface of the lower drain electrode **161**. The upper drain electrode **162** can be formed of the same material as that of the aforementioned upper source electrode **152**, for example, copper Cu, but not limited to this material. In order to lower a total resistance of the drain electrode **160**, a thickness of the upper drain electrode **162** is larger than a thickness of the lower drain electrode **161**, preferably.

The upper drain electrode **162** can be formed of the same material as that of the upper source electrode **152**, and the upper drain electrode **162** can be formed in the same thickness as that of the upper source electrode **152**. The lower drain electrode **161** can be formed of the same material as that of the lower source electrode **151**, and the lower drain electrode **161** can be formed in the same thickness as that of the lower source electrode **151**. In this instance, the drain electrode **160** and the source electrode **150** may be manufactured at the same time by the same process.

A structure of the thin film transistor layer (T) is not limited to the above structure, that is, a structure of the thin film transistor layer (T) can be changed to various shapes generally known to those in the art. For example, the drawing shows a top gate structure where the gate electrode **130** is provided over the active layer **110**, but not necessarily. That is, it is possible to provide a bottom gate structure where the gate electrode **130** is provided below the active layer **110**.

The passivation layer **165** is provided on the thin film transistor layer (T), and more particularly, on upper surfaces of the source electrode **150** and the drain electrode **160**. The passivation layer **165** protects the thin film transistor layer (T). The passivation layer **165** can be formed of an inorganic insulating material, for example, silicon oxide film SiOx or silicon nitride film SiNx, but not limited to these materials.

The first planarization layer **171** is provided on the passivation layer **165**. The first planarization layer **171** is provided to planarize an upper surface of the substrate **100** with the thin film transistor layer (T). The first planarization layer **171** can be formed of an organic insulating material, for example, acryl resin, epoxy resin, phenolic resin, polyamide resin, polyimide resin, and etc., but not limited to these materials.

The first anode electrode **180** and the first auxiliary electrode **190** are provided on the first planarization layer **171**. That is, the first anode electrode **180** and the first auxiliary electrode **190** are formed in the same layer. A third contact hole (CH3) for exposing the source electrode **150** is provided in the aforementioned passivation layer **165** and the first planarization layer **171**. The source electrode **150** and the first anode electrode **180** are connected to each other via the third contact hole (CH3). If needed, the third contact hole (CH3) can expose the drain electrode **160**, whereby the drain electrode **160** and the first anode electrode **180** can be connected to each other via the third contact hole (CH3).

The first anode electrode **180** can include a first lower anode electrode **181**, a first upper anode electrode **182**, and a first cover anode electrode **183**.

The first lower anode electrode **181** is provided between the planarization layer **170** and the first upper anode electrode **182**, in which the first lower anode electrode **181** enhances an adhesive strength between the planarization layer **170** and the first upper anode electrode **182**. Also, the first lower anode electrode **181** protects a lower surface of the first upper anode electrode **182**, to thereby prevent the lower surface of the first upper anode electrode **182** from being corroded. Thus, an oxidation degree of the first lower anode electrode **181** can be lower than an oxidation degree of the first upper anode electrode **182**. That is, a corrosion resistance in a material of the first lower anode electrode **181** can be superior to a corrosion resistance in a material of the first upper anode electrode **182**. Also, the first lower anode electrode **181** protects an upper surface of the upper source electrode **152**, to thereby prevent the upper surface of the upper source electrode **152** from being corroded. Thus, an oxidation degree of the first lower anode electrode **181** can be lower than an oxidation degree of the upper source electrode **152**. That is, a corrosion resistance in a material of the first lower anode electrode **181** can be superior to a corrosion resistance in a material of the upper source electrode **152**. Accordingly, it is possible to provide the aforementioned dual-layered structure in the source electrode **150** so the first lower anode electrode **180** prevents the upper surface of the upper source electrode **152** from becoming corroded. The first lower anode electrode **181** functions as an adhesion enhancement layer and/or a corrosion preventing layer. The first lower anode electrode **181** can be formed of an alloy MoTi of molybdenum and titanium, but not limited to this material.

The first upper anode electrode **182** is provided between the first lower anode electrode **181** and the first cover anode electrode **183**. The first upper anode electrode **182** can be formed of a low-resistance metal material such as copper Cu, but not limited to this metal material. The first upper anode electrode **182** can be formed of a metal material whose resistance is relatively lower than that of the first lower anode electrode **181** and the first cover anode electrode **183**. In order to lower a total resistance of the first anode electrode **180**, a thickness of the first upper anode electrode **182** is larger than a thickness of each of the first lower anode electrode **181** and the first cover anode electrode **183**, preferably.

The first cover anode electrode **183** is provided on the first upper anode electrode **182**. The first cover anode electrode **183** covers the upper and lateral surfaces of the first upper anode electrode **182** so that it is possible to prevent the upper and lateral surfaces of the first upper anode electrode **182** from being corroded. Thus, an oxidation degree of the first cover anode electrode **183** can be lower than an oxidation degree of the first upper anode electrode **182**. That is, a corrosion resistance in a material of the first cover anode electrode **183** can be superior to a corrosion resistance in a material of the first upper anode electrode **182**.

The first cover anode electrode **183** can cover the lateral surface of the first lower anode electrode **181**. In this instance, an oxidation degree of the first cover anode electrode **183** can be lower than an oxidation degree of the first lower anode electrode **181**. That is, a corrosion resistance in a material of the first cover anode electrode **183** can be superior to a corrosion resistance in a material of the first lower anode electrode **181**. The first cover anode electrode **183** can be formed of a transparent conductive material, for example, indium-tin-oxide ITO, but not limited to this material.

In the same manner as the first anode electrode **180**, the first auxiliary electrode **190** can include a first lower auxiliary electrode **191**, a first upper auxiliary electrode **192**, and a first cover auxiliary electrode **193**.

The first lower auxiliary electrode **191** is provided between the planarization layer **170** and the first upper auxiliary electrode **192**, in which the first lower auxiliary electrode **191** enhances an adhesive strength between the planarization layer **170** and the first upper auxiliary electrode **192**. Also, the first lower auxiliary electrode **191** prevents a lower surface of the first upper auxiliary electrode **192** from being corroded. Thus, an oxidation degree of the first lower auxiliary electrode **191** can be lower than an oxidation degree of the first upper auxiliary electrode **192**. That is, a corrosion resistance in a material of the first lower auxiliary electrode **191** can be superior to a corrosion resistance in a material of the first upper auxiliary electrode **192**. The first lower auxiliary electrode **191** can be formed of the same material as that of the first lower anode electrode **181**, that is, alloy MoTi of molybdenum and titanium, but not limited to this material.

The first upper auxiliary electrode **192** is provided between the first lower auxiliary electrode **191** and the first cover auxiliary electrode **193**. The first upper auxiliary electrode **192** can be formed of the same material as that of the first upper anode electrode **182**, that is, copper Cu, but not limited to this material. In order to reduce a total resistance of the first auxiliary electrode **190**, a thickness of the first upper auxiliary electrode **192** with the relatively-low resistance is larger than a thickness of each of the first lower auxiliary electrode **191** and the first cover auxiliary electrode **193** with the relatively-high resistance, preferably.

The first cover auxiliary electrode **193** is provided on the first upper auxiliary electrode **192**. The first cover auxiliary electrode **193** covers the upper and lateral surfaces of the first upper auxiliary electrode **192** so that it is possible to prevent the upper and lateral surfaces of the first upper auxiliary electrode **192** from being corroded. Thus, an oxidation degree of the first cover auxiliary electrode **193** can be lower than an oxidation degree of the first upper auxiliary electrode **192**. That is, a corrosion resistance in a material of the first cover auxiliary electrode **193** can be superior to a corrosion resistance in a material of the first upper auxiliary electrode **192**.

The first cover auxiliary electrode **193** can cover the lateral surface of the first lower auxiliary electrode **191**. In this instance, an oxidation degree of the first cover auxiliary electrode **193** can be lower than an oxidation degree of the first lower auxiliary electrode **191**. That is, a corrosion resistance in a material of the first cover auxiliary electrode **193** can be superior to a corrosion resistance in a material of the first lower auxiliary electrode **191**. The first cover auxiliary electrode **193** can be formed of a transparent conductive material, for example, indium-tin-oxide ITO, but not limited to this material.

The first cover auxiliary electrode **193** can be formed of the same material as that of the first cover anode electrode **183**, and the first cover auxiliary electrode **193** can be manufactured in the same thickness as that of the first cover anode electrode **183**. The first upper auxiliary electrode **192** can be formed of the same material as that of the first upper anode electrode **182**, and the first upper auxiliary electrode **192** can be manufactured in the same thickness as that of the first upper anode electrode **182**. The first lower auxiliary electrode **191** can be formed of the same material as that of the first lower anode electrode **181**, and the first lower auxiliary electrode **191** can be manufactured in the same

thickness as that of the first lower anode electrode **181**. In this instance, the first auxiliary electrode **190** and the first anode electrode **180** may be manufactured at the same time by the same process.

The second planarization layer **172** is provided on the first auxiliary electrode **190** and the first anode electrode **180**. The second planarization layer **172** together with the aforementioned first planarization layer **171** is provided to planarize the upper surface of the substrate **100**. The second planarization layer **172** can be formed of an organic insulating material, for example, acryl resin, epoxy resin, phenolic resin, polyamide resin, polyimide resin, and etc., but not limited to these materials.

A fourth contact hole (CH4) and a fifth contact hole (CH5) are provided in the second planarization layer **172**. The first anode electrode **180** is exposed via the fourth contact hole (CH4), and the first auxiliary electrode **190** is exposed via the fifth contact hole (CH5).

The second anode electrode **200** is provided on the second planarization layer **172**. The second anode electrode **200** is connected to the first anode electrode **180** via the fourth contact hole (CH4). The second anode electrode **200** reflects light emitted from the organic emitting layer **240** to an upper direction, whereby the second anode electrode **200** includes a material with good reflectance. The second anode electrode **200** can include a second lower anode electrode **201**, a second central anode electrode **202**, and a second upper anode electrode **203**.

The second lower anode electrode **201** is provided between the first anode electrode **180** and the second central anode electrode **202**. The second lower anode electrode **201** protects a lower surface of the second central anode electrode **202**, to thereby prevent the lower surface of the second central anode electrode **202** from being corroded. Thus, an oxidation degree of the second lower anode electrode **201** can be lower than an oxidation degree of the second central anode electrode **202**. That is, a corrosion resistance in a material of the second lower anode electrode **201** can be superior to a corrosion resistance in a material of the second central anode electrode **202**. The second lower anode electrode **201** can be formed of a transparent conductive material such as indium-tin-oxide ITO, but not limited to this material.

The second central anode electrode **202** is provided between the second lower anode electrode **201** and the second upper anode electrode **203**. The second central anode electrode **202** is formed of a material with relatively-low resistance and relatively-high reflectance in comparison to the second lower anode electrode **201** and the second upper anode electrode **203**, for example, argentums Ag, but not limited to this material. In order to lower a total resistance of the second anode electrode **200**, a thickness of the second central anode electrode **202** with relatively-low resistance is larger than a thickness in each of the second lower anode electrode **201** and the second upper anode electrode **203** with relatively-high resistance, preferably.

The second upper anode electrode **203** is provided on an upper surface of the second central anode electrode **202** so that it is possible to prevent the upper surface of the second central anode electrode **202** from being corroded. Thus, an oxidation degree of the second upper anode electrode **203** can be lower than an oxidation degree of the second central anode electrode **202**. That is, a corrosion resistance in a material of the second upper anode electrode **203** can be superior to a corrosion resistance in a material of the second central anode electrode **202**. The second upper anode elec-

trode **203** can be formed of a transparent conductive material such as indium-tin-oxide ITO, but not limited to this material.

In the same way as the aforementioned second anode electrode **200**, the second auxiliary electrode **210** is provided on the second planarization layer **172**. The second auxiliary electrode **210** is connected to the first auxiliary electrode **190** via the fifth contact hole (CH5). The second auxiliary electrode **210** together with the first auxiliary electrode **190** lowers a resistance of the cathode electrode **250**. Also, the second auxiliary electrode **210** prepares a gap space between the first bank **221** and the second bank **222**.

The second auxiliary electrode **210** can include a second lower auxiliary electrode **211**, a second central auxiliary electrode **212**, and a second upper auxiliary electrode **213**.

The second lower auxiliary electrode **211** is provided between the first auxiliary electrode **190** and the second central auxiliary electrode **212**. The second lower auxiliary electrode **211** protects a lower surface of the second central auxiliary electrode **212**, to thereby prevent the lower surface of the second central auxiliary electrode **212** from being corroded. Thus, an oxidation degree of the second lower auxiliary electrode **211** can be lower than an oxidation degree of the second central auxiliary electrode **212**. That is, a corrosion resistance in a material of the second lower auxiliary electrode **211** can be superior to a corrosion resistance in a material of the second central auxiliary electrode **212**. The second lower auxiliary electrode **211** can be formed of a transparent conductive material, for example indium-tin-oxide ITO, but not limited to this material.

A width of the second lower auxiliary electrode **211** is larger than a width of the second central auxiliary electrode **212** and a width of the second upper auxiliary electrode **213**, whereby it facilitates an electrical connection between the cathode electrode **250** and the second auxiliary electrode **210**.

The second central auxiliary electrode **212** is provided between the second lower auxiliary electrode **211** and the second upper auxiliary electrode **213**. The second central auxiliary electrode **212** is formed of a material with relatively-low resistance and relatively-high reflectance in comparison to the second lower auxiliary electrode **211** and the second upper auxiliary electrode **213**, for example, argentums Ag, but not limited to this material. In order to lower a total resistance of the second auxiliary electrode **210**, a thickness of the second central auxiliary electrode **212** with relatively-low resistance is larger than a thickness in each of the second lower auxiliary electrode **211** and the second upper auxiliary electrode **213** with relatively-high resistance, preferably.

A width of the second central auxiliary electrode **212** is smaller than a width of the second lower auxiliary electrode **211**. Also, the width of the second central auxiliary electrode **212** is smaller than a width of the second upper auxiliary electrode **213**. The second central auxiliary electrode **212** with the relatively-small width can increase the gap space between the first bank **221** and the second bank **222**, whereby the cathode electrode **250** is easily deposited in the gap space between the first bank **221** and the second bank **222**.

The second upper auxiliary electrode **213** is provided on an upper surface of the second central auxiliary electrode **212** so that it is possible to prevent the upper surface of the second central auxiliary electrode **212** from being corroded. Thus, an oxidation degree of the second upper auxiliary electrode **213** can be lower than an oxidation degree of the second central auxiliary electrode **212**. That is, a corrosion

resistance in a material of the second upper auxiliary electrode **213** can be superior to a corrosion resistance in a material of the second central auxiliary electrode **212**. The second upper auxiliary electrode **213** can be formed of a transparent conductive material such as indium-tin-oxide ITO, but not limited to this material.

Both ends of the second upper auxiliary electrode **213** upwardly extend along a lower surface of the first bank **221** (e.g., the ends of the second upper auxiliary electrode **213** form a type of "V" shaped cup that is wrapped around the bottom tip of the first bank **221**). A structure regarding the ends of the second upper auxiliary electrode **213** will be easily understood by the following manufacturing process.

The second upper auxiliary electrode **213** can be formed of the same material as that of the second upper anode electrode **203**, and the second upper auxiliary electrode **213** can be manufactured in the same thickness as that of the second upper anode electrode **203**. The second central auxiliary electrode **212** can be formed of the same material as that of the second central anode electrode **202**, and the second central auxiliary electrode **212** can be manufactured in the same thickness as that of the second central anode electrode **202**. The second lower auxiliary electrode **211** can be formed of the same material as that of the second lower anode electrode **201**, and the second lower auxiliary electrode **211** can be manufactured in the same thickness as that of the second lower anode electrode **201**.

According to one embodiment of the present invention, there are two auxiliary electrodes including the first auxiliary electrode **190** and the second auxiliary electrode **210** connected to each other for lowering the resistance of the cathode electrode **250**, thus it is possible to easily control the resistance properties of the auxiliary electrode.

In more detail, the second auxiliary electrode **210** is formed in the same layer as the second anode electrode **200**. Thus, if the width of the second auxiliary electrode **210** is increased, then the width of the second anode electrode **200** has to be decreased, which may decrease a pixel region of a display device. For this reason, there is a limit to increasing the width of the second auxiliary electrode **210**. According to one embodiment of the present invention, the first auxiliary electrode **190** connected to the second auxiliary electrode **210**, and provided below the second auxiliary electrode **210** so that it is possible to lower the resistance of the cathode electrode **250** without decreasing the pixel region.

The first auxiliary electrode **190** is formed in the same layer as the first anode electrode **180**, in which the first anode electrode **180** connects the source electrode **150** and the second anode electrode **200** with each other. Thus, it is possible to decrease the width of the first anode electrode **180**, and increase the width of the first auxiliary electrode **190**. That is, the width of the first auxiliary electrode **190** can be larger than the width of the first anode electrode **180**. Furthermore, since the width of the first auxiliary electrode **190** is increased, the first auxiliary electrode **190** can be overlapped with the second anode electrode **200**, in order to lower the resistance of the cathode electrode **250**.

The banks **221** and **222** are provided on the second anode electrode **200** and the second auxiliary electrode **210**, respectively. The banks **221** and **222** may include the first bank **221** and the second bank **222**. The first bank **221** and the second bank **222** are formed of the same material. The first bank **221** is provided on the upper surface of the second upper auxiliary electrode **213** of the second auxiliary electrode **210**. The second bank **222** is provided on the upper surface of the second anode electrode **200**, and the upper surface of the second lower auxiliary electrode **211** of the

second auxiliary electrode **210**. The first bank **221** and the second bank **222** are spaced apart from each other, and the second auxiliary electrode **210** and the cathode electrode **250** are electrically connected with each other in the gap space between the first bank **221** and the second bank **222**.

A thickness (t_2) of the second bank **222** is smaller than a thickness (t_1) of the first bank **221**. Since the thickness (t_2) of the second bank **222** is smaller than the thickness (t_1) of the first bank **221**, it facilitates the electrical connection between the cathode electrode **250** and the second auxiliary electrode **210** in the gap space between the first bank **221** and the second bank **222**. That is, if the thickness (t_2) of the second bank **222** is large, the interval between the first bank **221** and the second bank **222** is decreased, whereby the cathode electrode **250** might be not deposited in the gap space between the first bank **221** and the second bank **222**. In order to prevent this problem, the thickness (t_2) of the second bank **222** is smaller than the thickness (t_1) of the first bank **221**.

A width in an upper surface of the first bank **221** is larger than a width in a lower surface of the first bank **221**. Thus, the first bank **221** is formed in a structure of eaves. For example, the first bank **221** can have a reverse tapered shape or form a mushroom shape. From a top view, the gap space between the first bank **221** and the second bank **222** is covered by the upper surface of the first bank **221** having the structure of eaves so that it is possible to prevent the organic emitting layer **240** from being deposited in the gap space between the first bank **221** and the second bank **222** for a deposition process of the organic emitting layer **240**. That is, if the upper surface of the first bank **221** serving as the eaves is configured to cover the gap space between the first bank **221** and the second bank **222**, it is possible to prevent the organic emitting layer **240** from being permeated into the gap space between the first bank **221** and the second bank **222**. Accordingly, the second auxiliary electrode **210** can be exposed via the gap space between the first bank **221** and the second bank **222**. Especially, the organic emitting layer **240** can be manufactured by an evaporation method using a deposition material with superior straightness. Thus, the organic emitting layer **240** is not deposited in the gap space between the first bank **221** and the second bank **222** for the deposition process of the organic emitting layer **240**.

The second bank **222**, which exposes the upper surface of the second anode electrode **200**, is provided on one side and the other side of the second anode electrode **200** (e.g., the second anode electrode **200** is between two portions of the second bank **222**). Since the second bank **222** exposes the upper surface of the second anode electrode **200**, it is possible to secure an image-displaying area. Also, the second bank **222** is provided on one side and the other side of the second anode electrode **200**, in order to prevent the lateral surface of the second central anode electrode **202** from being exposed, in which the lateral surface of the second central anode electrode **202** is relatively vulnerable to corrosion, thereby preventing the lateral surface of the second central anode electrode **202** from being corroded.

Also, a portion of the second bank **222** is provided between the second anode electrode **200** and the second auxiliary electrode **210**, in which the second bank **222** electrically insulates the second anode electrode **200** and the second auxiliary electrode **210** from each other. The first bank **221** and the second bank **222** may be formed of an organic insulating material, for example, polyimide resin, acryl resin, benzocyclobutene BCB, and etc., but not limited to these materials.

The organic emitting layer **240** is provided on the second anode electrode **200**. The organic emitting layer **240** can include a hole injecting layer, a hole transporting layer, an emitting layer, an electron transporting layer, and an electron injecting layer. A structure of the organic emitting layer **240** can be changed to various shapes generally known to those in the art.

The organic emitting layer **240** can extend to the upper surface of the banks **221** and **222**. Also, the organic emitting layer **240** can extend to the upper surface of the second lower auxiliary electrode **211** of the second auxiliary electrode **210**. In this instance, the organic emitting layer **240** does not cover the entire upper surface of the second lower auxiliary electrode **211**. If the entire upper surface of the second lower auxiliary electrode **211** is covered by the organic emitting layer **240**, it is difficult to electrically connect the second auxiliary electrode **210** and the cathode electrode **250** with each other.

The cathode electrode **250** is provided on the organic emitting layer **240**. As the cathode electrode **250** is provided on a surface from which light is emitted, the cathode electrode **250** is formed of a transparent conductive material. Thus, a resistance of the cathode electrode **250** is increased since the cathode electrode **250** is formed of the transparent conductive material. In order to lower the resistance of the cathode electrode **250**, the cathode electrode **250** is connected to the second auxiliary electrode **210**. That is, the cathode electrode **250** is connected to the second auxiliary electrode **210** via the gap space between the first bank **221** and the second bank **222**. The cathode electrode **250** may be manufactured by sputtering, that is, a deposition process using a deposition material with inferior straightness. Accordingly, the cathode electrode **250** can be deposited in the gap space between the first bank **221** and the second bank **222** for the deposition process of the cathode electrode **250**.

Also, an encapsulation layer for preventing a permeation of moisture can be additionally provided on the cathode electrode **250**. The encapsulation layer can be formed of various materials generally known to those in the art. In addition, a color filter for each pixel can be additionally provided on the cathode electrode **250**. In this instance, white light may be emitted from the organic emitting layer **240**.

According to one embodiment of the present invention, instead of having an additional partition (See **70** of FIG. **1**) for providing an eaves structure, the width in the upper surface of the first bank **221** on the second auxiliary electrode **210** is made larger than the width in the lower surface of the first bank **221** so that the first bank **221** is able to serve as the eaves structure. In order words, a portion of the bank can be used to form the eaves structure. Thus, it is possible to omit an additional mask process for separately forming the partition (See **70** of FIG. **1**) according to the related art.

FIGS. **3A** to **3K** are cross sectional views illustrating a method of manufacturing the organic light emitting display device according to one embodiment of the present invention, which relate to the organic light emitting display device shown in FIG. **2**. Thus, the same reference numbers will be used throughout the drawings to refer to the same or like parts, and a detailed description for the same parts will be omitted or will be brief.

First, as shown in FIG. **3A**, the active layer **110**, the gate insulating film **120**, the gate electrode **130**, the insulating interlayer **140**, the source electrode **150**, and the drain electrode **160** are sequentially provided on the substrate **100**.

In more detail, the active layer **110** is provided on the substrate **100**, the gate insulating film **120** is provided on the active layer **110**, the gate electrode **130** is provided on the gate insulating film **120**, the insulating interlayer **140** is provided on the gate electrode **130**, the first and second contact holes (CH1, CH2) are provided in the gate insulating film **120** and the insulating interlayer **140**, and the drain electrode **160** connected to one end of the active layer **110** via the first contact hole (CH1) is provided and the source electrode **150** connected to the other end of the active layer **110** via the second contact hole (CH2) is provided.

The source electrode **150** can include the lower source electrode **151** and the upper source electrode **152**. The drain electrode **160** can include the lower drain electrode **161** and the upper drain electrode **162**.

Then, as shown in FIG. **3B**, the passivation layer **165** is provided on the source electrode **150** and the drain electrode **160**. The first planarization layer **171** is provided on the passivation layer **165**.

The third contact hole (CH3) is provided in the passivation layer **165** and the first planarization layer **171**, whereby the source electrode **150** is exposed to the external via the third contact hole (CH3). If needed, the drain electrode **160** can be exposed to the external via the third contact hole (CH3).

Then, as shown in FIG. **3C**, the first anode electrode **180** and the first auxiliary electrode **190** are provided on the first planarization layer **171**, in which the first anode electrode **180** and the first auxiliary electrode **190** are spaced apart from each other.

The first anode electrode **180** is connected with the source electrode **150** via the third contact hole (CH3). If the drain electrode **160** is exposed to the external via the third contact hole (CH3), the first anode electrode **180** is connected with the drain electrode **160** via the third contact hole (CH3).

The first anode electrode **180** can include the first lower anode electrode **181**, the first upper anode electrode **182**, and the first cover anode electrode **183**. The first auxiliary electrode **190** can include the first lower auxiliary electrode **191**, the first upper auxiliary electrode **192**, and the first cover auxiliary electrode **193**.

The first anode electrode **180** and the first auxiliary electrode **190** can be formed of the same material, and can be manufactured at the same time by the same patterning process.

Then, as shown in FIG. **3D**, the second planarization layer **172** is provided on the first anode electrode **180** and the first auxiliary electrode **190**.

The fourth contact hole (CH4) and the fifth contact hole (CH5) are provided in the second planarization layer **173**. The first anode electrode **180** is exposed to the external via the fourth contact hole (CH4), and the first auxiliary electrode **190** is exposed to the external via the fifth contact hole (CH5).

Then, as shown in FIG. **3E**, the second anode electrode **200** and the second auxiliary electrode **210** are provided on the second planarization layer **172**.

The second anode electrode **200** and the second auxiliary electrode **210** can be formed of the same material, and can be manufactured at the same time by the same patterning process.

The second anode electrode **200** can include the second lower anode electrode **201**, the second central anode electrode **202**, and the second upper anode electrode **203**. The second auxiliary electrode **210** can include the second lower auxiliary electrode **211**, the second central auxiliary electrode **212**, and the second upper auxiliary electrode **213**.

Then, as shown in FIG. 3F, photoresist patterns **410** and **420** are provided on the second anode electrode **200** and the second auxiliary electrode **210**.

The photoresist patterns **410** and **420** can include the first photoresist pattern **410** provided on the second auxiliary electrode **210**, and the second photoresist pattern **420** provided on the second anode electrode **200**.

The first photoresist pattern **410** is provided on a predetermined portion of an upper surface of the second auxiliary electrode **210**, whereby one side and the other side of the second auxiliary electrode **210** are not covered by the first photoresist pattern **410**.

The second photoresist pattern **420** is provided on an entire upper surface of the second anode electrode **200**, whereby an entire portion of the second anode electrode **200** is covered by the second photoresist pattern **420**.

As shown in FIG. 3G, a predetermined portion of the second auxiliary electrode **210** is etched by using the first photoresist pattern **410** as a mask.

In detail, one side and the other side of the second auxiliary electrode **210**, which are not covered by the first photoresist pattern **410**, are etched away. In this instance, the second lower auxiliary electrode **211** is not etched, but the second central auxiliary electrode **212** and the second upper auxiliary electrode **213** are etched. That is, under the condition that the first photoresist pattern **410** is used as the mask, the second upper auxiliary electrode **213** is etched first, and then the second central auxiliary electrode **212** is etched. Thus, the second lower auxiliary electrode **211** is not etched. However, if needed, the second lower auxiliary electrode **211** may be partially etched.

After the etching process, the width of the second upper auxiliary electrode **213** may be the same as the width of the first photoresist pattern **410**, however, the width of the second central auxiliary electrode **212** provided under the second upper auxiliary electrode **213** may be smaller than the width of the first photoresist pattern **410**. Accordingly, the width of the second upper auxiliary electrode **213** obtained after the etching process may be larger than the width of the second central auxiliary electrode **212** obtained after the etching process.

The second anode electrode **200** is covered by the second photoresist pattern **420**, whereby the second anode electrode **200** is not etched by the etching process of the second auxiliary electrode **210**.

Then, as shown in FIG. 3H, the first photoresist pattern **410** and the second photoresist pattern **420** are removed, and then the banks **221** and **222** are provided on the second auxiliary electrode **210** and the second anode electrode **200**, respectively.

The banks **221** and **222** can include the first bank **221** provided on the upper surface of the second upper auxiliary electrode **213** of the second auxiliary electrode **210**, and the second bank **222** provided on the remaining regions. The second bank **222** is provided on the upper surface of the second anode electrode **200**, and provided on the upper surface of the second lower auxiliary electrode **211** of the second auxiliary electrode **210**.

The thickness (t_2) of the second bank **222** is smaller than the thickness (t_1) of the first bank **221**. Since the thickness (t_2) of the second bank **222** is smaller than the thickness (t_1) of the first bank **221**, it facilitates the electrical connection between the second auxiliary electrode **210** and the cathode electrode (See **250** of FIG. 3K) in the gap space between the first bank **221** and the second bank **222**.

That is, if the thickness (t_2) of the second bank **222** is large, the interval between the first bank **221** and the second

bank **222** becomes small, whereby the cathode electrode (See **250** of FIG. 3K) might be not deposited in the gap space between the first bank **221** and the second bank **222** for the following process of FIG. 3K. Thus, in order to prevent this problem, the thickness (t_2) of the second bank **222** is smaller than the thickness (t_1) of the first bank **221**. The first bank **221** and the second bank **222** which have the different thicknesses can be manufactured by one exposure through the use of half-tone mask or diffraction mask.

Then, as shown in FIG. 3I, a thermal treatment is carried out to induce a thermal stress between the first bank **221** and the second upper auxiliary electrode **213** provided below the first bank **221**. That is, the first bank **221** shrinks as it is heated so that both ends of the lower surface of the first bank **221** are decreased in width. Accordingly, both ends of the second upper auxiliary electrode **213** upwardly extend along the lower surface of the first bank **221** (e.g., heating the first bank **221** causes the ends of the second upper auxiliary electrode **213** to bend upward, thus forming a type of cup around the bottom tip of the first bank **221**).

By the aforementioned process, the width in the upper surface of the first bank **221** is larger than the width in the lower surface of the first bank **221**, whereby it is possible to obtain the structure of eaves in the first bank **221**. For example, the first bank **221** can have a reverse tapered shape or form a mushroom shape. Owing to the structure of eaves, the gap space between the first bank **221** and the second bank **222** is covered by the upper surface of the first bank **221** (e.g., the overhanging part of the first bank **221**). Thus, it is possible to prevent the organic emitting layer **240** from being deposited in the gap space between the first bank **221** and the second bank **222** for the following deposition process of the organic emitting layer **240**.

Then, as shown in FIG. 3J, the organic emitting layer **240** is provided on the second anode electrode **200**.

The organic emitting layer **240** may be manufactured by an evaporation method using a deposition material with superior straightness. Thus, the organic emitting layer **240** can be deposited on the upper surface of the banks **221** and **222**. However, it is possible to prevent the organic emitting layer **240** from being deposited in the gap space between the first bank **221** and the second bank **222**. That is, the upper surface of the first bank **221** serves as the eaves for the deposition process of the organic emitting layer **240**, whereby it is possible to prevent the organic emitting layer **240** from being deposited in the gap space between the first bank **221** and the second bank **222** for the deposition process of the organic emitting layer **240** without using the mask pattern of covering the upper surface of the second lower auxiliary electrode **211**.

However, some of the organic emitting layer **240** may be deposited in the gap space between the first bank **221** and the second bank **222**. Even in this instance, all of the second lower auxiliary electrode **211** is not covered by the organic emitting layer **240**.

As shown in FIG. 3K, the cathode electrode **250** is provided on the organic emitting layer **240**.

The cathode electrode **250** is connected to the second auxiliary electrode **210** via the gap space between the first bank **221** and the second bank **222**. The cathode electrode **250** can be manufactured by sputtering, that is, a deposition process using a deposition material with inferior straightness. Accordingly, the cathode electrode **250** can be deposited in the gap space between the first bank **221** and the second bank **222** for the deposition process of the cathode electrode **250**. Especially, the cathode electrode **250** can be respectively connected with the second lower auxiliary

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electrode **211**, the second central auxiliary electrode **212**, and the second upper auxiliary electrode **213** constituting the second auxiliary electrode **210**.

According to one embodiment of the present invention, the first bank **221** provided on the second auxiliary electrode **210** is configured to have the structure of eaves so that it is possible to omit the additional mask process for forming the partition according to the related art.

According to one embodiment of the present invention, there are the two auxiliary electrodes including the first auxiliary electrode **190** and the second auxiliary electrode **210** for lowering the resistance of the cathode electrode **250**, in order to easily control the resistance properties of the auxiliary electrode. Especially, the first auxiliary electrode **190** is connected with the second auxiliary electrode **210** via the contact hole and the first auxiliary electrode **190** is provided below the second auxiliary electrode **210** so that it is possible to lower the resistance of the cathode electrode **250** without decreasing the pixel region.

It will be apparent to those skilled in the art that various modifications and variations can be made in the present invention without departing from the spirit or scope of the inventions. Thus, it is intended that the present invention covers the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An organic light emitting display (OLED) device comprising:

a substrate;

an anode electrode on the substrate;

an organic emitting layer on the anode electrode;

a cathode electrode on the organic emitting layer;

an auxiliary electrode connected with the cathode electrode;

a first bank on an upper surface of the auxiliary electrode; and

a second bank disposed between the auxiliary electrode and the anode electrode, wherein the second bank is formed of a same material as the first bank, and the first and second banks are spaced apart from each other, wherein a width of an upper surface of the first bank is larger than a width of a lower surface of the first bank, and the cathode electrode is connected with the auxiliary electrode via a gap space between the first bank and the second bank.

2. The OLED device according to claim 1, wherein the first bank and a portion of the auxiliary electrode form a partition having a reverse tapered shape that narrows towards a bottom of the partition, and

wherein the partition has eaves and the cathode electrode is connected to the auxiliary electrode in an area under the eaves of the partition.

3. The OLED device according to claim 1, wherein the portion of the auxiliary electrode forms a base of the partition and the first bank forms an upper portion of the partition.

4. The OLED device according to claim 1, wherein the auxiliary electrode includes a lower auxiliary electrode, a central auxiliary electrode, and an upper auxiliary electrode.

5. The OLED device according to claim 4, wherein a width of the lower auxiliary electrode is larger than a width of each of the central auxiliary electrode and the upper auxiliary electrode, and the width of the central auxiliary electrode is smaller than the width of the upper auxiliary electrode.

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6. The OLED device according to claim 4, wherein both ends of the upper auxiliary electrode upwardly extend along a lower surface of the first bank.

7. The OLED device according to claim 4, wherein the first bank is provided on an upper surface of the upper auxiliary electrode, and the second bank is provided on an upper surface of the lower auxiliary electrode.

8. The OLED device according to claim 1, wherein a thickness of the first bank is larger than a thickness of the second bank.

9. The OLED device according to claim 1, wherein the anode electrode includes a first anode electrode, and a second anode electrode connected with the first anode electrode via a contact hole,

wherein the auxiliary electrode includes a first auxiliary electrode, and a second auxiliary electrode connected with the first auxiliary electrode via a contact hole, and wherein the first bank is provided on the second auxiliary electrode, and the second bank is provided between the second auxiliary electrode and the second anode electrode.

10. The OLED device according to claim 9, wherein a width of the first auxiliary electrode is larger than a width of the first anode electrode, and the first auxiliary electrode overlaps with the second anode electrode.

11. The OLED device according to claim 9, wherein a width of the second anode electrode is larger than a width of the first anode electrode, and the second anode electrode overlaps with the first auxiliary electrode.

12. The OLED device according to claim 9, wherein the first auxiliary electrode or the second auxiliary electrode comprises a layered structure including a central auxiliary electrode disposed between an upper auxiliary electrode and a lower auxiliary electrode, and

wherein the upper and lower auxiliary electrodes include a material having a higher corrosion resistance than the central auxiliary electrode, and the central auxiliary electrode includes a material having a lower electrical resistance than the upper and lower auxiliary electrodes.

13. The OLED device according to claim 12, wherein the upper auxiliary electrode of the first auxiliary electrode covers lateral surfaces of the central and lower auxiliary electrodes of the first auxiliary electrode.

14. The OLED device according to claim 1, wherein the auxiliary electrode comprises a first auxiliary electrode and a second auxiliary electrode, and the second auxiliary electrode overlaps with and connects to the first auxiliary electrode,

wherein the anode electrode comprises a first anode electrode and a second anode electrode, and the second anode electrode overlaps with and connects to the first auxiliary electrode, and

wherein the first or second anode electrode is formed on a same layer as the first or second auxiliary electrode.

15. An organic light emitting display (OLED) device comprising:

an organic emitting layer disposed on a first pixel electrode;

a second pixel electrode disposed on the organic emitting layer;

an auxiliary electrode connected with the second pixel electrode;

a first bank disposed on the auxiliary electrode;

a second bank including a first portion and a second portion, wherein the first and second portions of the

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second bank are disposed on sides of the first bank and on ends of the auxiliary electrode; and
a gap space between the first bank and the first or second portion of the second bank,
wherein the auxiliary electrode connects to the second pixel electrode in the gap space between the second bank and the first or second bank portion.

16. The OLED device according to claim 15, wherein the first bank and a portion of the auxiliary electrode form a partition having a reverse tapered shape that narrows towards a bottom surface of the partition, and
wherein the partition has eaves and the cathode electrode is connected to the auxiliary electrode in an area under the eaves of the partition.

17. The OLED device according to claim 15, wherein the first bank and the second bank are made from a same material.

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